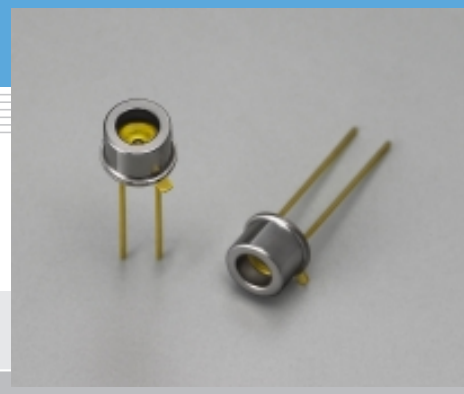


Infrared LED

L8245

Peak emission wavelength: 1.65 μm



L8245 is a long-wavelength infrared LED using an InGaAs chip. The peak emission occurs at a wavelength near the methane gas absorption band, making L8245 ideal for a light source for methane gas detection.

Features

- Peak emission wavelength: 1.65 μm
- High radiant output

Applications

- Light source for methane gas detection

■ Absolute maximum ratings (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Condition	Value	Unit
Reverse voltage	VR Max.		1	V
Forward current	IF		80	mA
Forward current decrease rate	-		1.1	mA/°C
Pulse forward current	IFP	Pulse width=10 μs Duty ratio=1 %	1.0	A
Pulse forward current decrease rate	-		13	mA/°C
Power dissipation	P		150	mW
Operating temperature	Topr		-30 to +85	°C
Storage temperature	Tstg		-40 to +100 ^{*1}	°C

*1: Guaranteed to resist temperature cycle test of up to 5 cycles.

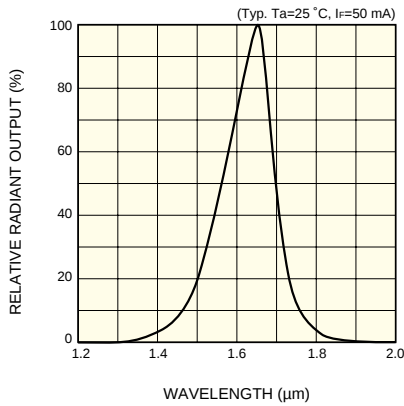
■ Electrical and optical characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak emission wavelength	λ_p	IF=50 mA	1.6	1.65	1.7	μm
Spectral half width	$\Delta\lambda$	IF=50 mA	-	130	-	nm
Radiant flux	ϕ_e	IF=50 mA	0.5	0.8	-	mW
Forward voltage	VF	IF=50 mA	-	1.0	1.5	V
Reverse current	IR	VR=1 V	-	-	10	μA
Cut-off frequency	fc	IF=50 mA $\pm$ 10 mAp-p, ^{*2}	1	3	-	MHz

*2: Frequency at which the optical output decreases by -3 dB versus a reference output level at 100 kHz.

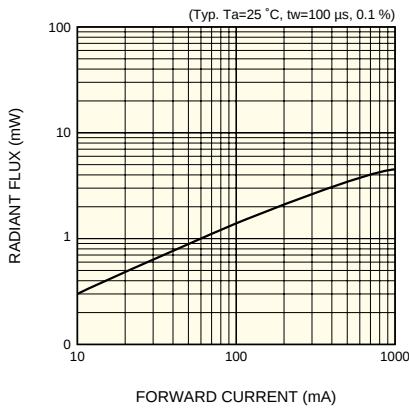
L8245 may be damaged or performance may deteriorate due to static electricity, so use caution when handling.

■ Emission spectrum



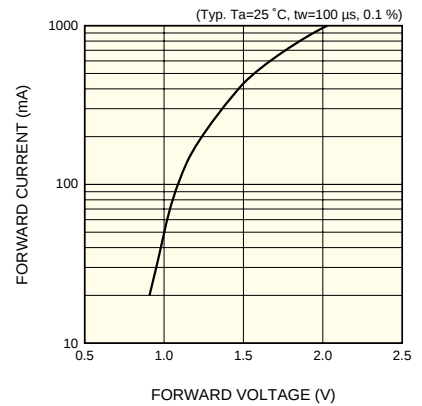
KLEDB0222EA

■ Radiant flux vs. forward current



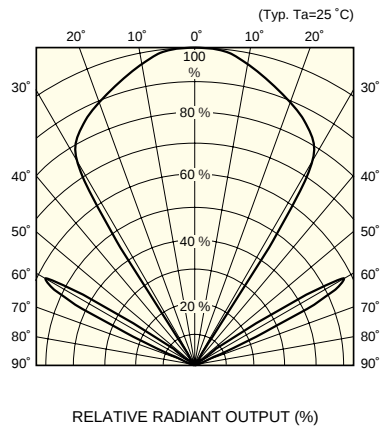
KLEDB0229EA

■ Forward current vs. forward voltage



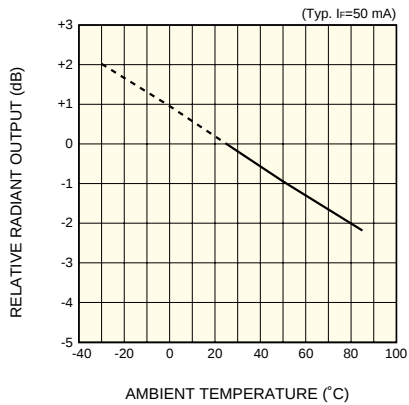
KLEDB0229EA

■ Directivity



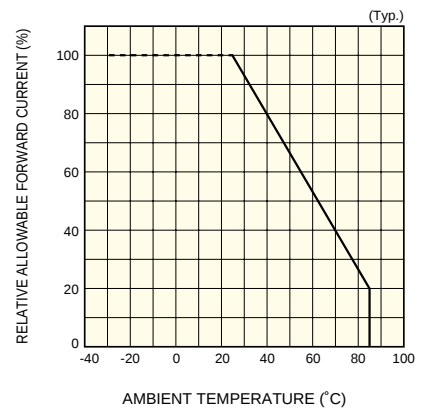
KLEDB0223EA

■ Radiant output vs. ambient temperature



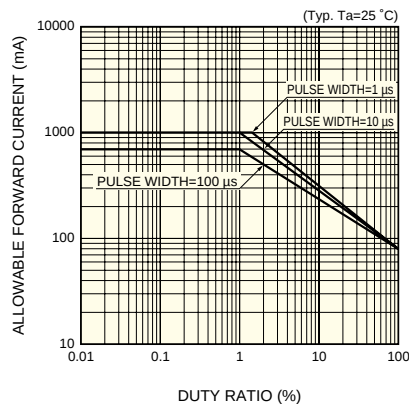
KLEDB0224EA

■ Allowable forward current vs. ambient temperature



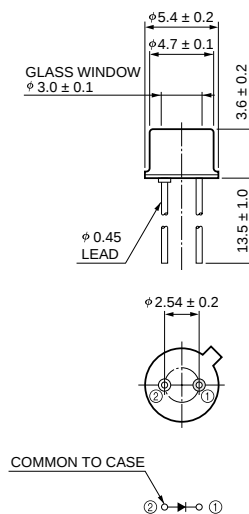
KLEDB0027EB

■ Allowable forward current vs. duty ratio



KLEDB0225EA

■ Dimensional outline (unit: mm)



KLEDA0071EA

HAMAMATSU

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